

STSA851

Low voltage fast-switching NPN power transistor

Features

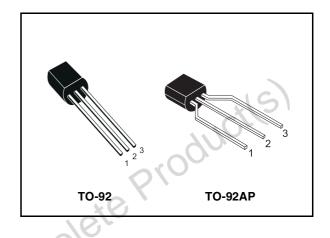
- Very low collector to emitter saturation voltage
- High current gain characteristic
- Fast-switching speed

Applications

- Emergency lighting
- Voltage regulators
- Relay drivers
- High efficiency low voltage switching applications

Description

The device is manufactured in NPN planar technology by using a "base island" layout. the resulting transistor shows exceptional high gain performance coupled with very low saturation voltage.



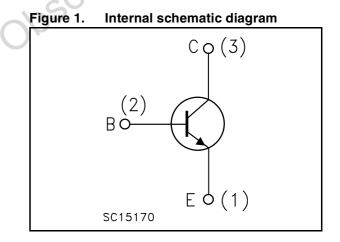


Table 1.	Device	summary

Order code	Marking	Package	Packaging
STSA851	SA851	TO-92	Bulk
STSA851-AP	SA851	TO-92AP	Ammopack

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	duct(s)
	* Proc
-10S	plete
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Electrical ratings 1

Table 2. Absolute maximum rat	ing
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Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	150	V
V_{CEO}	Collector-emitter voltage (I _B = 0)	60	V
V_{EBO}	Emitter-base voltage (I _C = 0)	7	V
۱ _C	Collector current	5	А
I _{CM}	Collector peak current (t _P < 5 ms)	20	А
Ι _Β	Base current	1,6	А
P _{tot}	Total dissipation at T _{amb} = 25 °C	<u> </u>	W
T _{stg}	Storage temperature -65 to		°C
Т _Ј	Max. operating junction temperature	150	°C
Table 3.	Thermal data		
_			

Table 3. Thermal data

	Symbol	nbol Parameter		Value	Unit
	R _{thj-amb}	Thermal resistance junction-ambient	max	114	°C/W
0105018	teP	roductls			

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2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

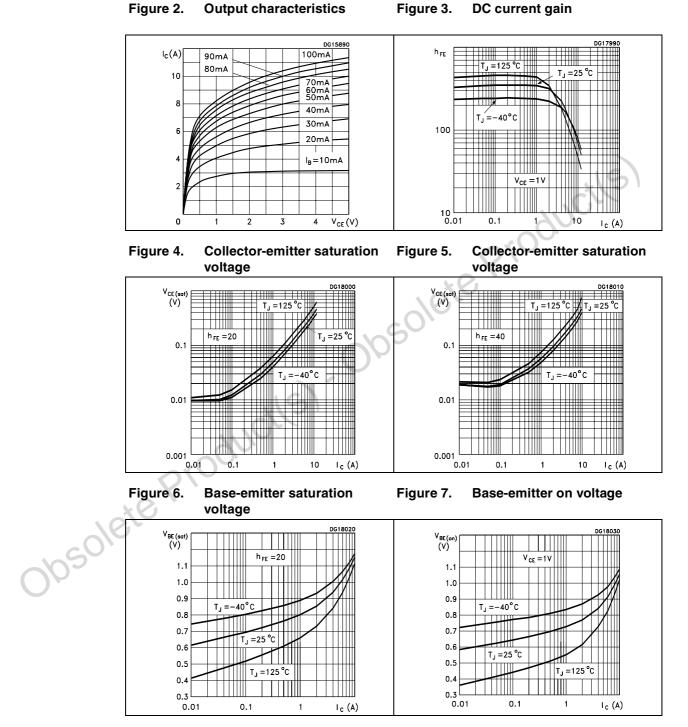
	Table 4.	Electrical characteristics						
Symbol		Parameter	Test co	onditions	Min.	Тур.	Max.	Unit
	I _{CBO}	Collector cut-off current	V _{CB} = 120 V				50	nA
	.080	(I _E = 0)	V _{CB} = 120 V	T _C = 100 °C			1	μA
	I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 7 V				10	nA
	V _{(BR)CBO} ⁽¹⁾	Collector-base breakdown Voltage (I _E = 0)	I _C = 100 μA		150	20	J.C.	v
	V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown Voltage (I _B = 0)	I _C = 10 mA	×eF	60			V
	V _{(BR)EBO} ⁽¹⁾	Emitter-base breakdown Voltage $(I_{C} = 0)$	I _E = 100 μA	plere	7			v
			l _C = 100 mA	I _B = 5 mA		10	50	mV
	V _{CE(sat)} ⁽¹⁾	Collector-emitter	I _C = 1 A	I _B = 50 mA		70	120	mV
	02(000)	saturation voltage	I _C = 2 A	I _B = 50 mA		140	200	mV
		CL	I _C = 5 A	I _B = 200 mA		320	450	mV
	V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage	I _C = 4 A	I _B = 200 mA		1	1.15	V
	0		I _C = 10 mA	$V_{CE} = 1 V$	150	300		
	h	DC aurrent asia	I _C = 2 A	$V_{CE} = 1 V$	150	270	350	
10	hFE	DC current gain	I _C = 5 A	$V_{CE} = 1 V$	90	140		
JK.			I _C = 10 A	$V_{CE} = 1 V$	30	50		
	f _T	Transition frequency	V _{CE} = 10 V	I _C = 100 mA		130		MHz
ole	C _{CBO}	Collector-base capacitance	V _{CB} = 10 V	f = 1 MHz		45		pF
		Resistive load						
	t _{on}	Turn-on time	I _C = 1 A	V _{CC} = 10 V		55		ns
	t _s	Storage time	$I_{B1} = -I_{B2} = 0.$	1 A		1.35		μs
	t _f	Fall time				120		ns

Table 4.	Electrical	characteristics

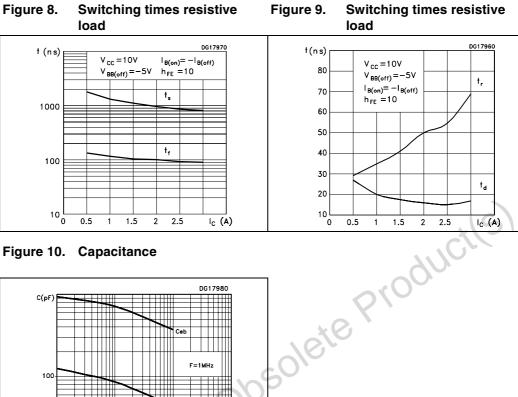
1. Pulsed duration = 300 μ s, duty cycle \ge 1.5%.

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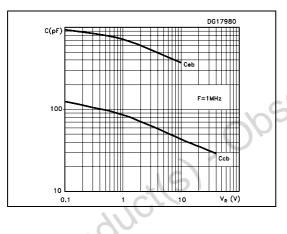
2.1 Electrical characteristics (curves)



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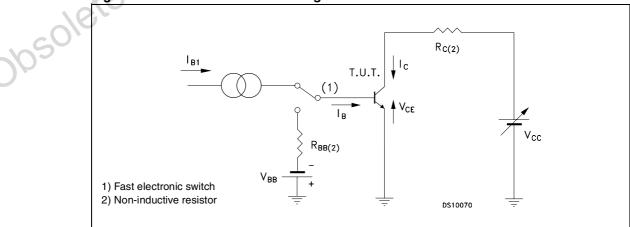






2.2 **Test circuit**

Figure 11. Resistive load switching test circuit



3 Package mechanical data

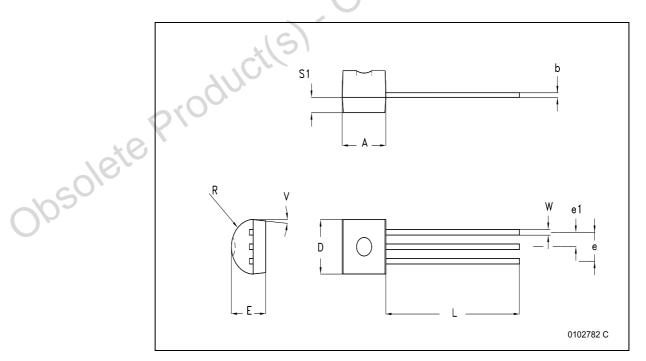
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Obsolete Product(s). Obsolete Product(s)

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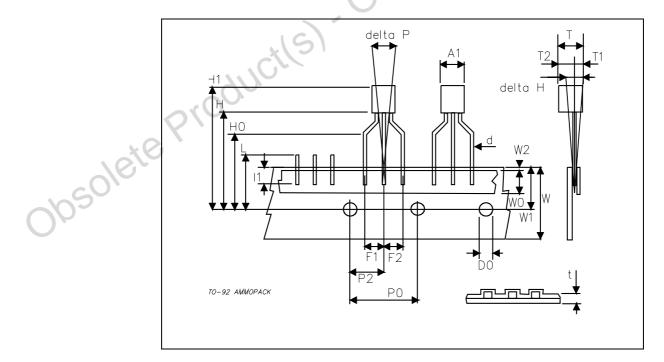
DIM.		mm.	
	MIN.	ТҮР	MAX.
A	4.32		4.95
b	0.36		0.51
D	4.45		4.95
E	3.30		3.94
е	2.41		2.67
e1	1.14		1.40
L	12.70	0	15.49
R	2.16	.0.	2.41
S1	0.92	1610	1.52
W	0.41	<u> </u>	0.56
V		5 ⁰	







DIM.		mm.	
DIM.	MIN.	ТҮР	MAX.
A1			4.80
Т			3.80
T1			1.60
T2			2.30
d			0.48
P0	12.50	12.70	12.90
P2	5.65	6.35	7.05
F1,F2	2.44	2.54	2.94
delta H	-2.00		2.00
W	17.50	18.00	19.00
W0	5.70	6.00	6.30
W1	8.50	9.00	9.25
W2			0.50
Н	18.50		20.50
H0	15.50	16.00	16.50
H1			25.00
D0	3.80	4.00	4.20
t			0.90
L			11.00
11	3.00		
delta P	-1.00		1.00



TO-92 AMMOPACK SHIPMENT (Suffix"-AP") MECHANICAL DATA

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4 Revision history

Table 5.Document revision history

Date	Revision	Changes
05-Sep-2003	2	
25-Mar-2008	3	New graphics.

obsolete Product(s). Obsolete Product(s)

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